

INA6017AM1

FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

INA6017AM1 is a silicon PNP transistor.
It is designed with high voltage.

FEATURE

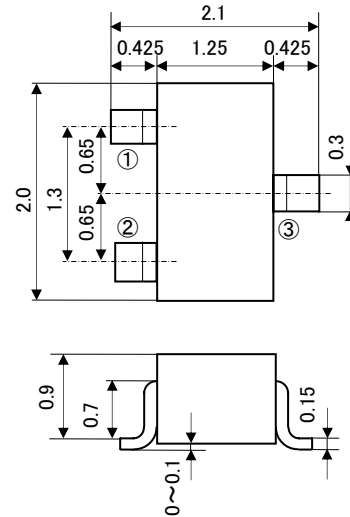
- Small package for easy mounting.
- High voltage $V_{CEO} = -150V$
- Low voltage $V_{CE(sat)} = -0.2V(\text{MAX})$

APPLICATION

High voltage switching.

OUTLINE DRAWING

UNIT : mm



Terminal Connector

JEITA: SC-70

①: Base

JEDEC: -

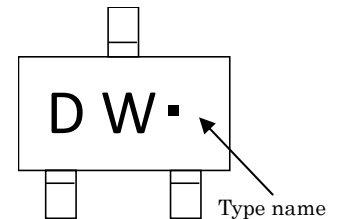
②: Emitter

③: Collector

MAXIMUM RATING ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to Base voltage	-160	V
V_{EBO}	Emitter to Base voltage	-5	V
V_{CEO}	Collector to Emitter voltage	-150	V
I_{CM}	Peak collector current	-200	mA
I_C	Collector current	-100	mA
P_C	Collector dissipation($T_a=25^\circ\text{C}$)	200	mW
T_j	Junction temperature	+150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 ~ +150	$^\circ\text{C}$

MARKING



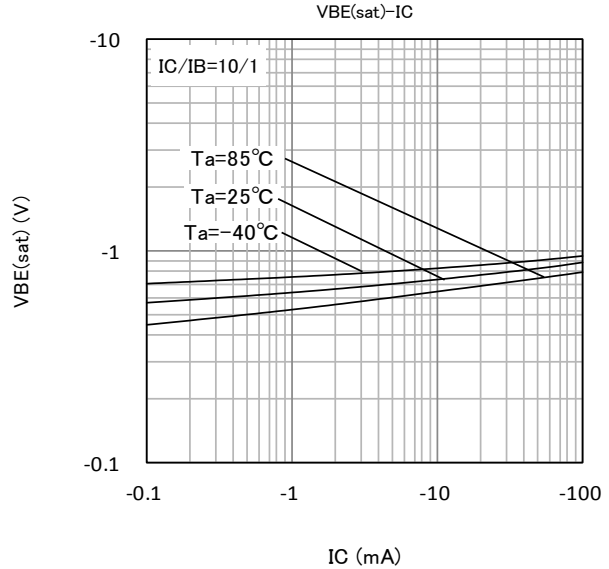
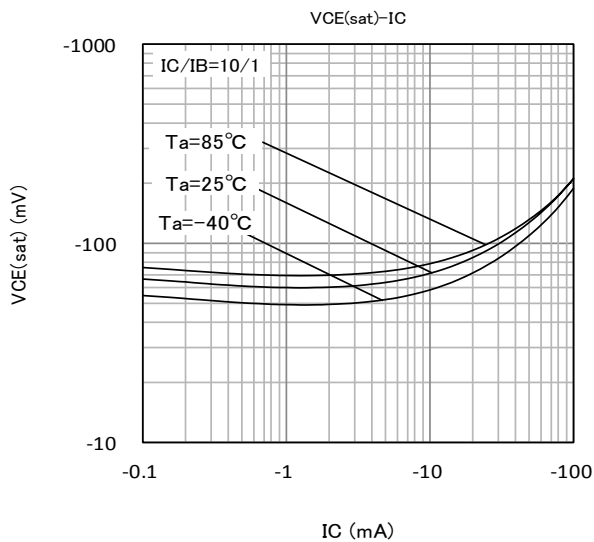
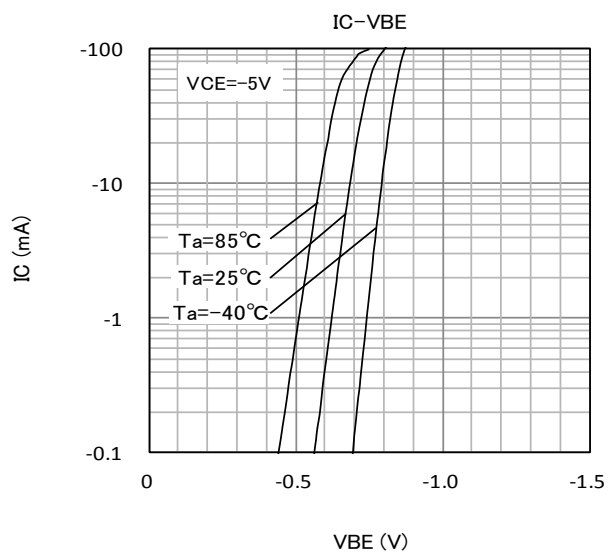
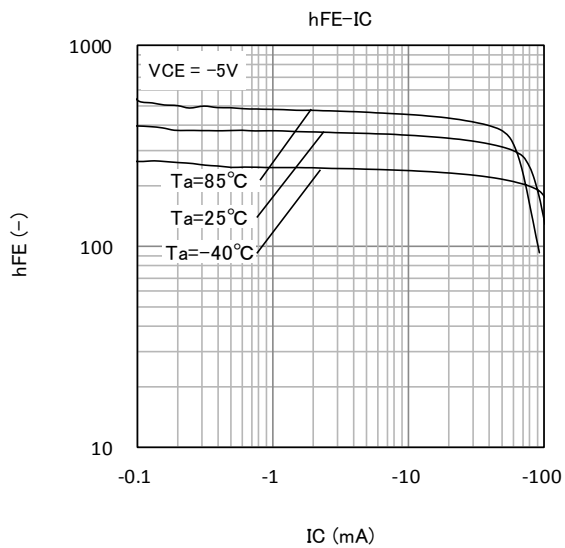
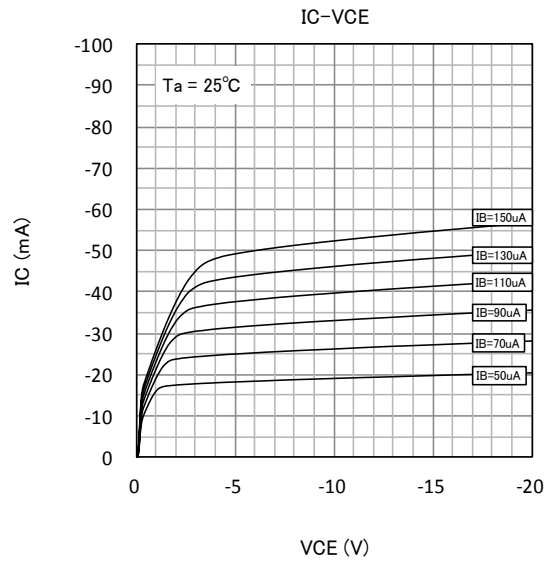
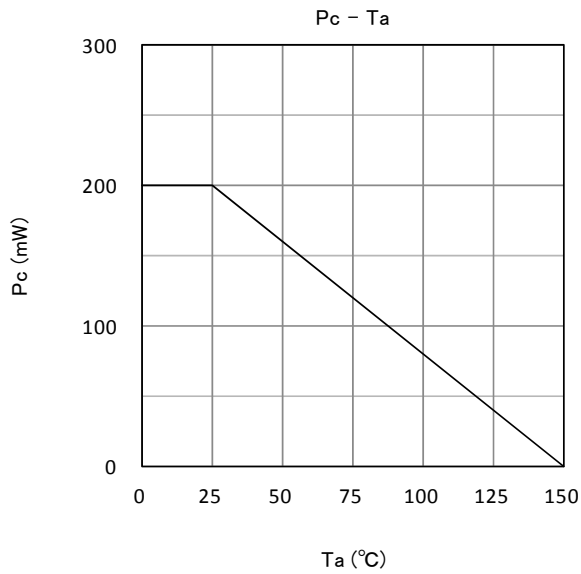
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CBO}$	C to B breakdown voltage	$I_C = -100\mu\text{A}, I_E = 0$	-160	-	-	V
$V_{(BR)EBO}$	E to B breakdown voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5	-	-	V
$V_{(BR)CEO}$	C to E breakdown voltage	$I_C = -1\text{mA}, R_{BE} = \infty$	-150	-	-	V
I_{CBO}	Collector cut off current	$V_{CB} = -120V, I_E = 0$	-	-	-100	nA
I_{EBO}	Emitter cut off current	$V_{EB} = -3V, I_C = 0$	-	-	-100	nA
hFE1	DC forward current gain1	$V_{CE} = -5V, I_C = -1\text{mA}$	150	-	-	-
hFE2	DC forward current gain2	$V_{CE} = -5V, I_C = -10\text{mA}$	200	-	500	-
hFE3	DC forward current gain3	$V_{CE} = -5V, I_C = -50\text{mA}$	45	-	-	-
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-	-	-0.2	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-	-	-1.0	V
fT	Gain bandwidth product	$V_{CE} = -10V, I_E = 10\text{mA}$	-	130	-	MHz
Cob	Collector output capacitance	$V_{CB} = -10V, I_E = 0, f = 1\text{MHz}$	-	3	-	pF

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TYPICAL CHARACTERISTICS





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